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34. (Amended) The device of claim 7 wherein said insulating film comprising aluminum nitride has a thickness of 100 Å to 5000 Å.

35. (Amended) The device of claim 8 wherein said insulating film has a thickness of 100 Å to 5000 Å.

39. (Amended) The display of claim 21 wherein said aluminum nitride insulating film has a thickness of 100 Å to 5000 Å.

43. (Amended) The device of claim 2 wherein said channel formation region is crystallized by laser irradiation through a layer comprising at least one of silicon oxide and [silicon nitride] on said channel formation region.

44. (Amended) The device of claim 3 wherein said channel formation region is crystallized by laser irradiation through a layer comprising at least one of silicon oxide and [silicon nitride] on said channel formation region.

45. (Amended) The device of claim 6 wherein said channel formation region is crystallized by laser irradiation through a layer comprising at least one of silicon oxide and [silicon nitride] on said channel formation region.

46. (Amended) The device of claim 7 wherein said channel formation region is crystallized by laser irradiation through a layer comprising at least one of silicon oxide and [silicon nitride] on said channel formation region.

47. (Amended) The device of claim 8 wherein said channel formation region is crystallized by laser irradiation through a layer comprising at least one of silicon oxide and [silicon nitride] on said channel formation region.

48. (Amended) The device of claim 19 wherein said channel formation region is crystallized by laser irradiation through a layer comprising at least one of silicon oxide and [silicon nitride] on said channel formation region.

49. (Amended) The device of claim 20 wherein said channel formation region is crystallized by laser irradiation through a layer comprising at least one of silicon oxide and [silicon nitride] on said channel formation region.

50. (Amended) The device of claim 21 wherein said channel formation region is crystallized by laser irradiation through a layer comprising at least one of silicon oxide and [silicon nitride] on said channel formation region.